KBP308GA-E

SINGLE PHASE GLASS PASSIVATED BRIDGE RECTIFIER

Voltage: 800V Current:3.0A

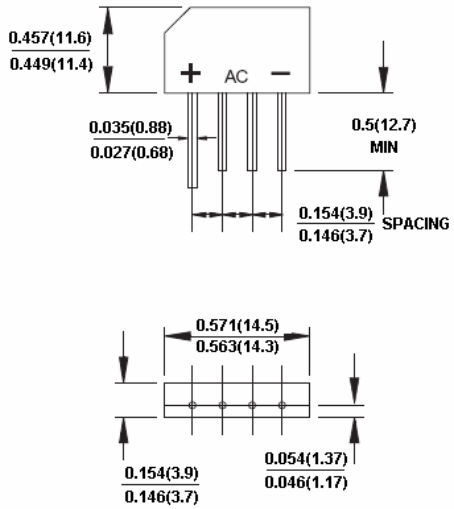
Features

Glass passivated chip junction
High case dielectric strength
High surge current capability
Ideal for printed circuit board
Halogen Free

Mechanical Data

Terminal: Plated leads solderable per J-STD-002
Case: UL-94 Class V-0 recognized Halogen Free Epoxy
Polarity: Polarity symbol marked on body
Mounting position: any

KBP



Dimensions in millimeters

MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

(single-phase, half -wave, 60HZ, resistive or inductive load rating at 25°C, unless otherwise stated)

	Symbol	KBP308GA-E	units
Maximum repetitive peak reverse voltage	Vrrm	800	V
Maximum RMS voltage	Vrms	560	V
Maximum DC blocking voltage	Vdc	800	V
Maximum average forward rectified output current Ta =55℃	If(av)	3.0	A
Peak forward surge current single sine-wave superimposed on rated load (JEDEC Method)	Ifsm	90	A
Maximum instantaneous forward voltage drop per leg at 3.0A	Vf	1.05	V
Rating for fusing (t < 8.3ms)	I^2t	32	A^2Sec
Maximum DC reverse current at Ta = 25°C rated DC blocking voltage per leg Ta = 125°C	Ir	5.0 500	μA
Maximum thermal resistance per leg (Note1)	Rth(ja) Rth(jc)	30 11	℃/W
Typical junction capacitance per leg at 4.0V,1MHz	Cj	25	pF
Operating junction and storage temperature range	Tj, Tstg	-55 to +150	℃

Note:
1. Thermal resistance from junction to ambient and from junction to lead mounted on P.C.B. with 0.47 x 047" (12 x 12mm) copper pads

RATINGS AND CHARACTERISTIC CURVES KBP308GA-E

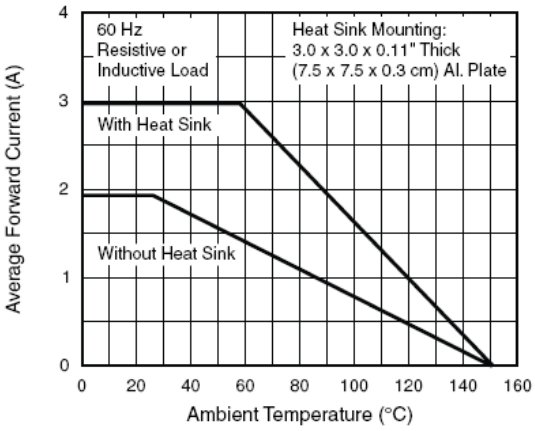


Figure 1. Forward Current Derating Curve

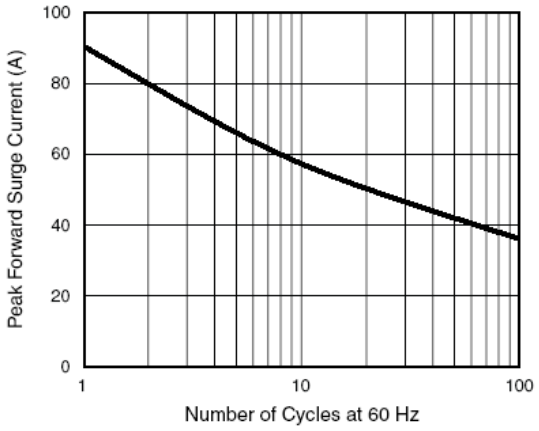


Figure 2. Maximum Non-Repetitive Peak Forward Surge Current Per Diode

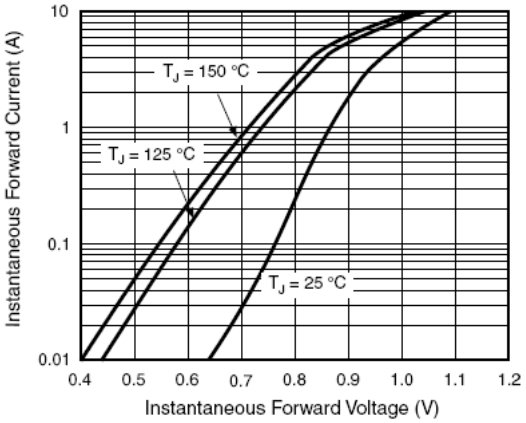


Figure 3. Typical Forward Characteristics Per Diode

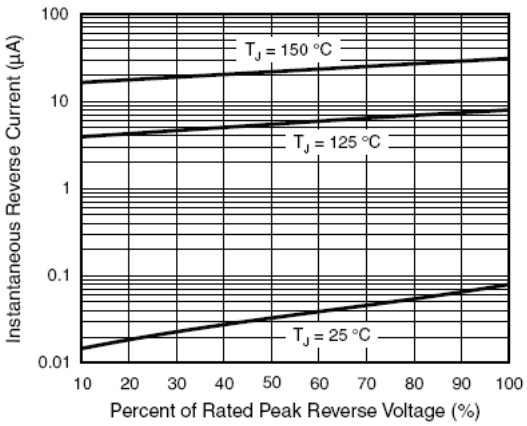


Figure 4. Typical Reverse Leakage Characteristics Per Diode

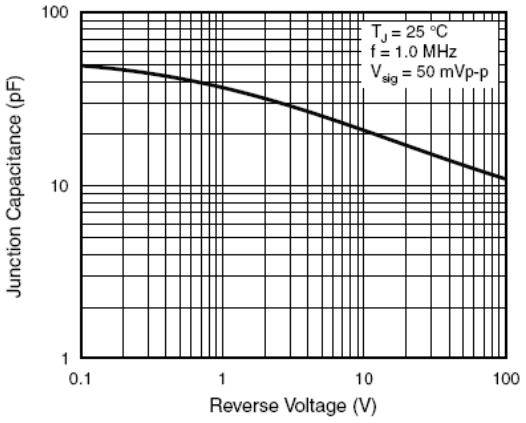


Figure 5. Typical Junction Capacitance Per Diode